

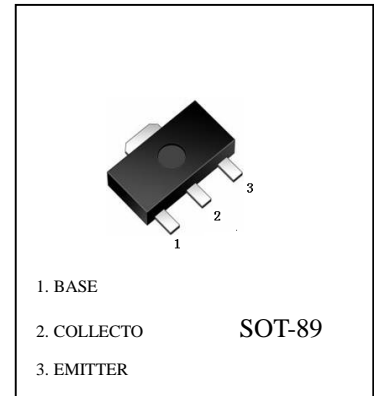
FEATURES

- Complementary to 2SC2884

2SA1664 (PNP)

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-35	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-800	mA
Collector Power dissipation	PC	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55to +150	°C



ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =-1mA, I _E =0	-35			V
Collector- emitter breakdown voltage	V _{CEO}	I _C =-10mA, I _B =0	-30			V
Emitter- base breakdown voltage	V _{EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-35V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-100mA	100		320	
		V _{CE} =-1V, I _C =-700mA	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-20mA			-0.7	V
Base-emitter	V _{BE}	V _{CE} =-1V, I _C =-10mA	-0.5		-0.8	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		19		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	RO	RY